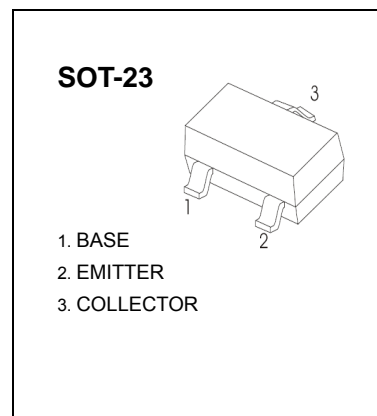


SOT-23 Plastic-Encapsulate Transistors

1SS226 SWITCHING DIODE

FEATURES

- Low forward voltage
- Fast reverse recovery time
- Small total capacitance



MARKING: C3

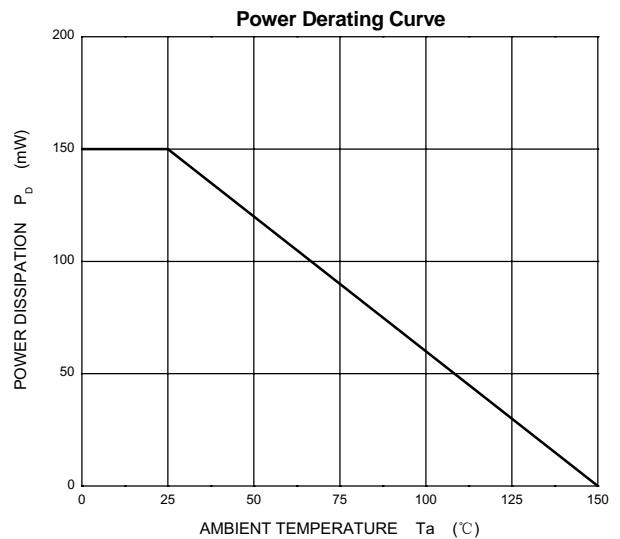
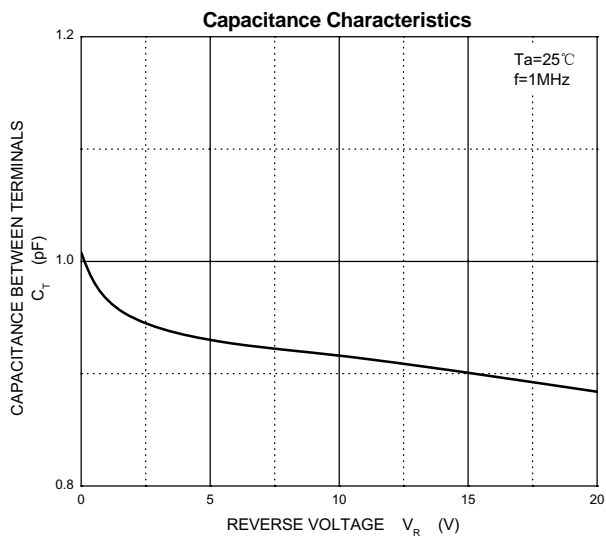
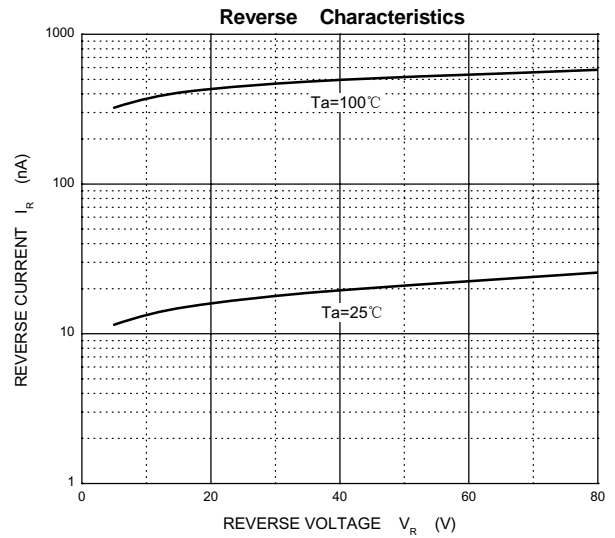
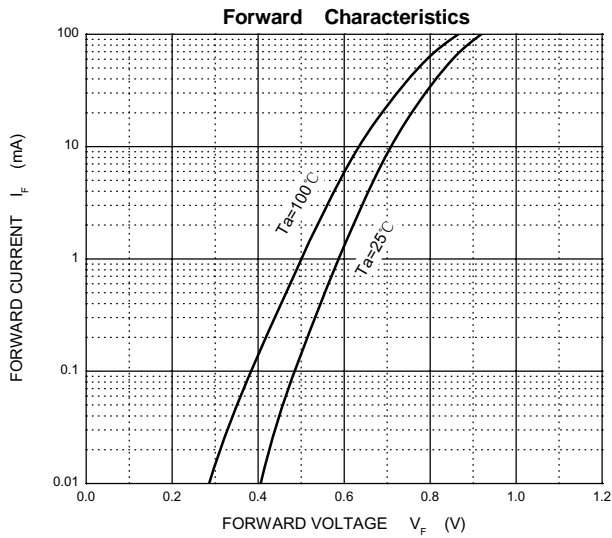
Maximum Ratings ,Single Diode @Ta=25°C

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	85	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}	80	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	100	mA
Peak Forward Surge Current @t=10ms	I_{FSM}	2	A
Power Dissipation	P_D	150	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

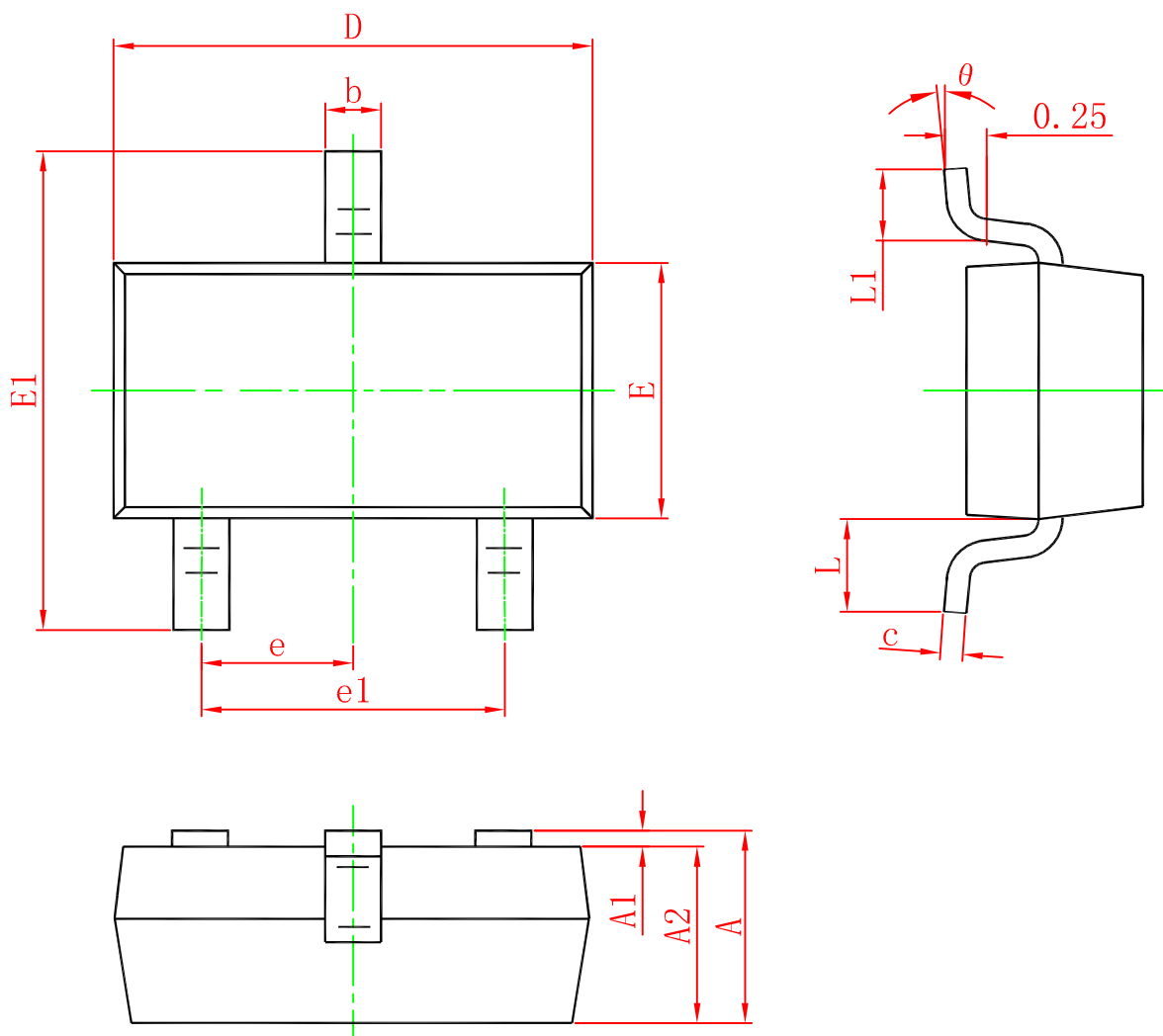
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	80		V
Reverse voltage leakage current	I_R	$V_R=80V$		0.5	μA
Forward voltage	V_F	$I_F=100mA$		1.2	V
Diode capacitance	C_D	$V_R=0V, f=1MHz$		3	pF
Reverse recovery time	t_{rr}	$I_F=10mA$		4	ns

SOT-23 Plastic-Encapsulate Transistors



SOT-23 Plastic-Encapsulate Transistors

SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°